

# KSU13003H

**SemiHow**  
Know-How for Semiconductor

# KSU13003H

## Switch Mode series NPN silicon Power Transistor

- High Voltage, High Speed Switching
- Suitable for switching regulator, inverters motor controls

2 Amperes  
NPN Silicon Power Transistor  
25 Watts

### Absolute Maximum Ratings TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	900	V
Collector-Emitter Voltage	$V_{CEO}$	530	V
Emitter-Base Voltage	$V_{EBO}$	9	V
Collector Current(DC)	$I_C$	2	A
Collector Current(Pulse)	$I_{CP}$	4	A
Base Current	$I_B$	1	A
Collector Dissipation(Tc=25°C)	$P_C$	25	W
Storage Temperature	$T_{STG}$	-55~150	°C
Max. Operating Junction Temperature	$T_J$	150	°C

TO-251  
1. Base  
2. Collector  
3. Emitter



### Electrical Characteristics TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	$V_{CBO}$	$I_C=500\mu A, I_E=0$	900			V
Collector-Emitter Breakdown Voltage	$V_{CEO}$	$I_C=10mA, I_B=0$	530			V
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=9V, I_C=0$			10	$\mu A$
*DC Current Gain	$h_{FE1}$ $h_{FE2}$	$V_{CE}=10V, I_C=0.4A$ $V_{CE}=10V, I_C=1A$	20 6		40	
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=0.1A$ $I_C=1.5A, I_B=0.5A$			0.8 2.5	V V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=0.5A, I_B=0.1A$			1.0	V
Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=0.1MHz$		21		pF
Current Gain Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=0.1A$	4			MHz
Turn on Time	$t_{on}$	$V_{CC}=125V, I_C=2A$ $I_{B1}=0.2A, I_{B2}=-0.2A$ $R_L=125\Omega$			1.1	$\mu s$
Storage Time	$t_{stg}$				4.0	$\mu s$
Fall Time	$t_F$				0.7	$\mu s$

\* Pulse Test: Pulse Width $\leq$ 300 $\mu s$ , Duty Cycle $\leq$ 2%

Note.

hFE1 Classification	R	20 ~ 30
	O	25 ~ 35
	Y	30 ~ 40

Package Mark information.

S H 13003 YWW Z	S	SemiHow Symbol
	YWW	Y; year code, WW; week code
	Z	hFE1 Classification

# Typical Characteristics

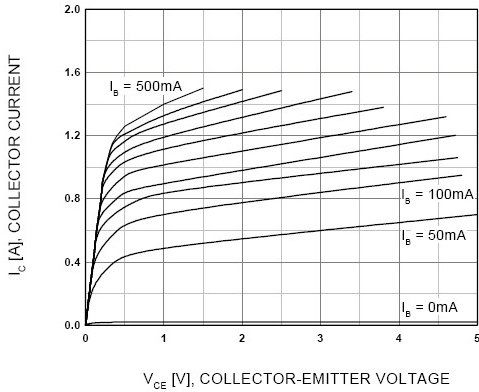


Figure 1. Static Characteristic

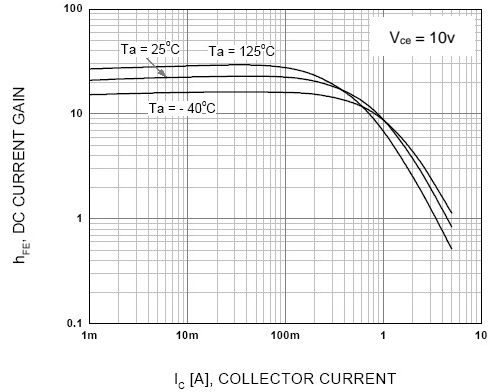


Figure 2. DC current Gain

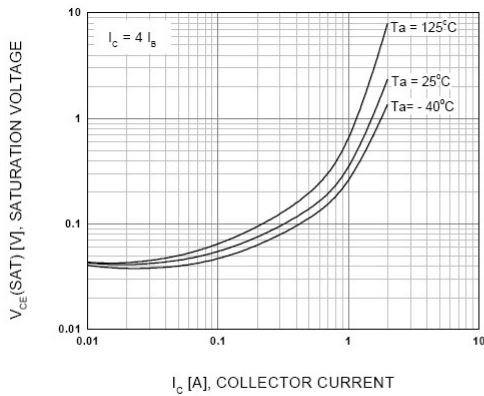


Figure 3. Collector-Emitter Saturation Voltage

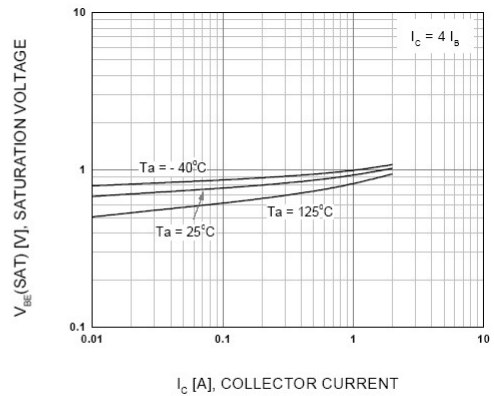


Figure 4. Base-Emitter Saturation Voltage

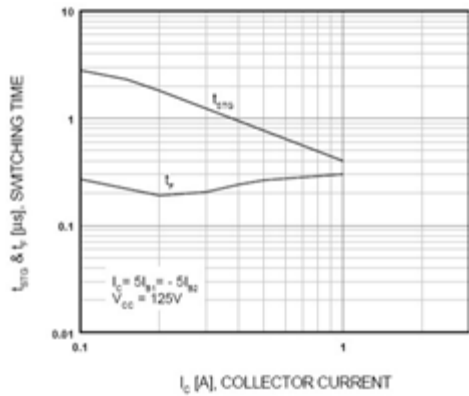


Figure 5. Resistive Load Switching Time

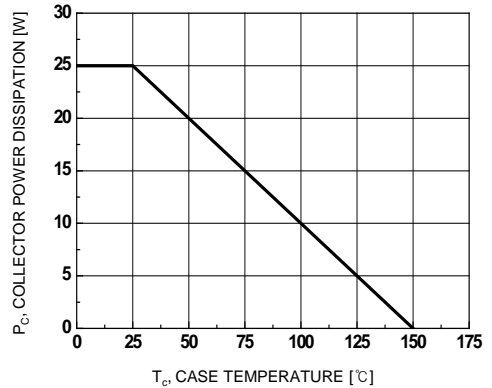


Figure 6. Power Derating

### Typical Characteristics

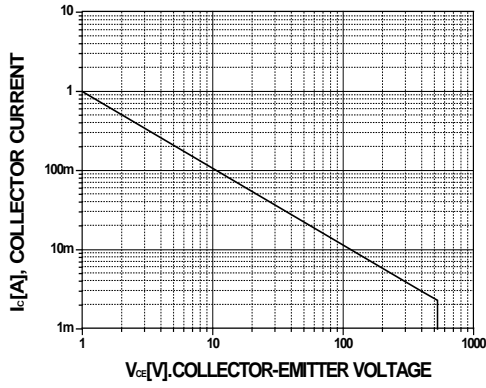


Figure 7. Forward Bias Safe Operating Area

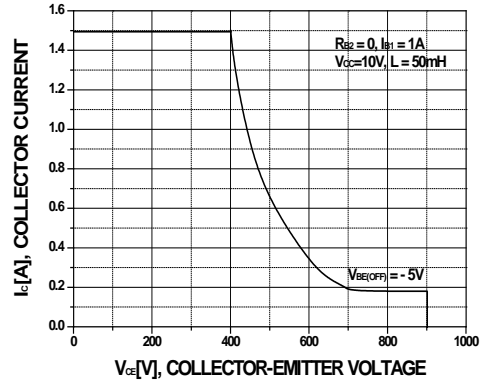


Figure 8. Reverse Bias Safe Operating Area

Package Dimension

TO-251

